



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	18mΩ @ V _{GS} = 10V	43A
	$20m\Omega @ V_{GS} = 4.5V$	41A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Power Management Functions
- DC-DC Converters
- Industrial

Features

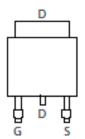
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

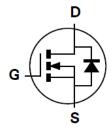
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

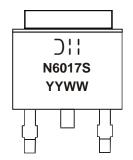
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6017SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Dili=Manufacturer's Marking
N6017S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
0 ($T_C = +25$ °C $T_C = +70$ °C	ID	43 34	А
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	11 8.8	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	70	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	3.6	Α	
Avalanche Current, L = 0.1mH	I _{AS}	25	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	32	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Bower Dissinction (Note 5)	$T_A = +25^{\circ}C$	D	3.3	- W
Total Power Dissipation (Note 5)	$T_C = +25^{\circ}C$	P _D	50	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	38	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	2.5	*C/VV	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

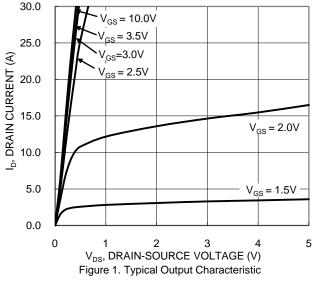
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

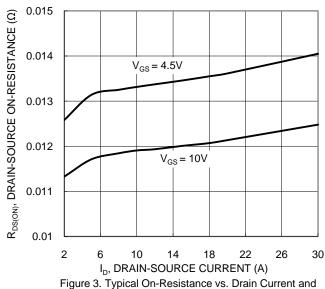
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance)	-	-	18	mΩ	$V_{GS} = 10V, I_D = 6A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	20	11177	$V_{GS} = 4.5V, I_{D} = 4A$	
Diode Forward Voltage	V _{SD}	-	-	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)	0 00 70						
Input Capacitance	C _{iss}	ı	2711	-	рF	45)()(
Output Capacitance	Coss	-	152	-	рF	V _{DS} = 15V, V _{GS} = 0V, - f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	-	126	-	pF		
Gate Resistance	R_{g}	-	1.4	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	26	-	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	-	55	-	nC	10)/ 1 60	
Gate-Source Charge	Q _{qs}	-	6.2	-	nC	$V_{DS} = 48V, I_{D} = 6A$	
Gate-Drain Charge	Q_{gd}	-	8.5	-	nC		
Turn-On Delay Time	t _{D(ON)}	-	4.9	-	ns		
Turn-On Rise Time	t _R	-	5.4	-	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	-	38.2	-	ns	$R_g = 3.3\Omega$, , $I_D = 6A$	
Turn-Off Fall Time	t _F	-	11	-	ns	7	
Reverse Recovery Time	t _{RR}	-	16.6	-	ns	L CA 4:/4t 400A/	
Reverse Recovery Charge	Q_{RR}	-	10.3	-	nC	$I_F = 6A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







Gate Voltage

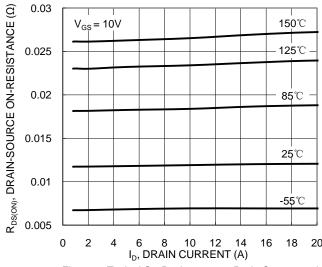
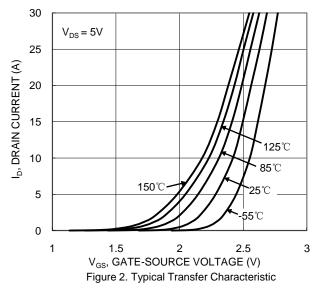
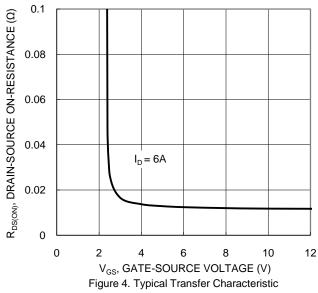


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





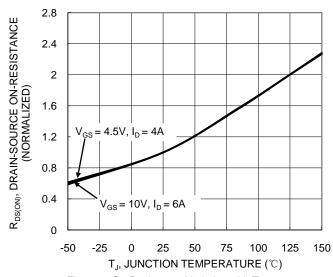


Figure 6. On-Resistance Variation with Temperature





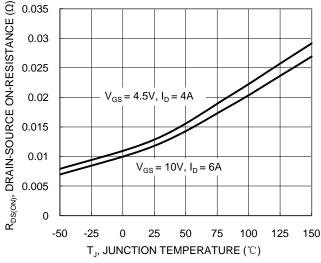


Figure 7. On-Resistance Variation with Temperature

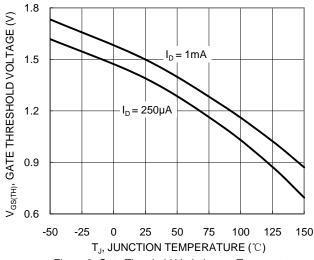
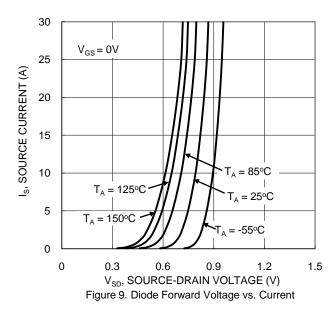


Figure 8. Gate Threshold Variation vs. Temperature



10000 f=1MHz C_T, JUNCTION CAPACITANCE (pF) $\mathbf{C}_{\mathrm{iss}}$ 1000 $\mathsf{C}_{\mathsf{oss}}$ 100 $\mathbf{C}_{\mathrm{rss}}$ 10 0 15 20 25 30 35 40 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 11. Typical Junction Capacitance

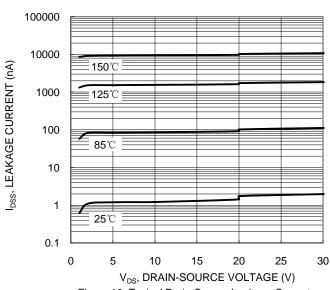
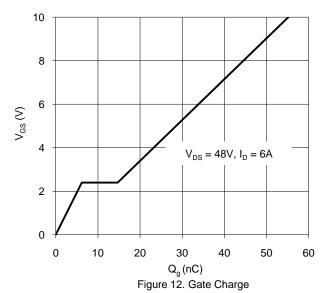
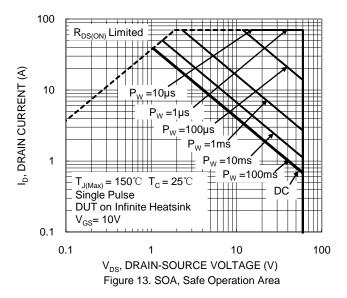


Figure 10. Typical Drain-Source Leakage Current vs. Voltage







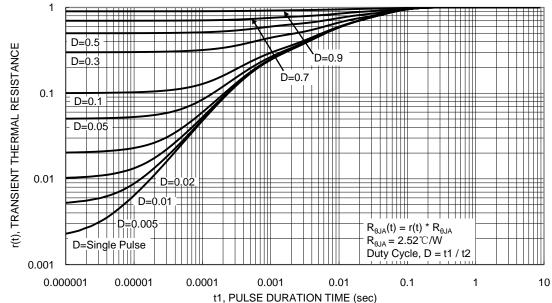
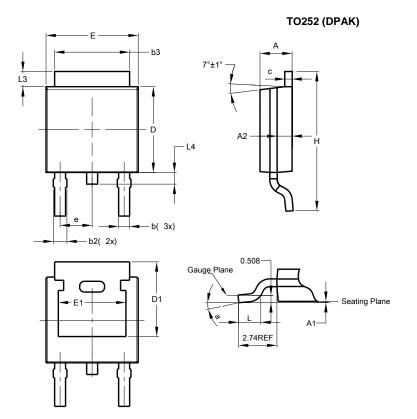


Figure 14. Transient Thermal Resistance



Package Outline Dimensions

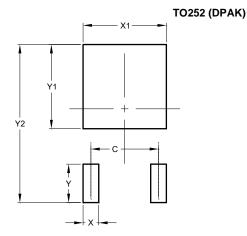
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)				
С	4.572				
Х	1.060				
X1	5.632				
Υ	2.600				
Y1	5.700				
V2	10.700				



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